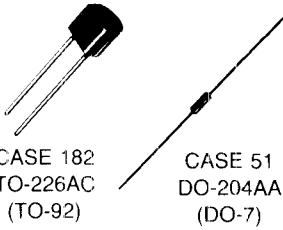


RF — SIGNAL PROCESSING DIODES (continued)

General-Purpose Tuning Diodes (continued)

High-Capacitance Tuning Diodes . . . for tuning applications in lower RF frequencies.



MAXIMUM WORKING VOLTAGE							
20 VOLTS				12 VOLTS			
CASE 182				CASE 51			
Cap Ratio 2-20 V Min	Q @ 4.0 V 20 MHz Min	Device		Cap Ratio 2-10 V Min	Q @ 2.0 V 1.0 MHz Min	Device	
C _T Nominal Capacitance pF ±10% (@ V _R = 4.0 V f = 1.0 MHz	120	2.3	250	MV2301	10	200	MV1404, H**(2)
	150	2.3	250	MV2302	10	200	MV1403, H**(2)
	180	2.3	200	MV2303			
	200	2.3	200	MV2304			
	220	2.3	150	MV2305			
	250	2.3	150	MV2306	10	200	MV1405, H**(2)
	270	2.3	100	MV2307			
	330	2.3	100	MV2308			

(1) C_T tolerance is ±20%.
(2) V_R = 2.0 V
**100% processing on "H" devices.

100% Processing For High Reliability

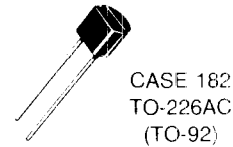
Hot-Carrier Diodes

Hot-Carrier diodes are ideal for VHF and UHF mixer and detector applications as well as many higher frequency applications. They provide stable electrical characteristics by eliminating the point-contact diode presently used in many applications.

V _{(BR)R} I _R = 10 μA Volts Min	C _T f = 1.0 MHz pF Max @ V _R Volts	V _F I _F = 10 mA Volts Max	I _R nA Max @ V _R Volts	NF f = 1.0 GHz dB Max	Device	Package		
4.0	10	0	0.6	250	3.0	7.0	MBD101	TO-226AC
20	1.5	15	0.6	200	15	—	MBD201	
30	1.5	15	0.6	200	25	—	MBD301	
50	1.0	20	1.2	200	25	—	MBD501	
70	1.0	20	1.2	200	35	—	MBD701	

Pin Switching Diodes

. . . designed for VHF band switching and general-purpose switching.



V _{(BR)R} I _R = 10 μAdc Volts Min	R _S I _F = 10 mAdc f = 10 MHz Ohms Max	C _T f = 1.0 MHz pF Max	L _S f = 250 MHz nH Typ	C _C f = 1.0 MHz pF Typ	Device	Package
20	0.85	2.0 (@ 15 V)	6.0	0.18	MPN3404	TO-226AC
200	1.0	1.0 (@ 20 V)	1.0	0.18	MPN3700	